

Recipe SU8-2050
50 um

Dehydration at 120 C for 10 min.

Dispense negative photoresist (SU8-2050) on silicon wafer

Spin coating to achieve 50- μ m thickness:

Spin at 300 RPM for 15 sec.

Spin at 3000 RPM for 30 sec.

Soft bake:

5 min. at 70C

10min. at 90C

Exposure Energy: 180 mJ/cm²(20sec in MJB-6)

Post exposure:

5min. at 70C

10min. at 90C

Ramp down 50C.

Development 10 min.(in su8 developer)

Surface development – IPA

Hard bake: 110C for 10 min.

Recipe SU8-2100
100 um

Dehydration at 120 C for 10 min.

Dispense negative photoresist (SU8-2100) on silicon wafer

Spin coating to achieve 100- μ m thickness:

Spin at 300 RPM for 15 sec.

Spin at 3000 RPM for 30 sec.

Soft bake:

Ramp up from 50°C

10 min. at 70°C

75min. at 90°C

Exposure Energy: 500 mJ/cm²

Post exposure:

10min. at 70°C

35 min. at 90°C

Ramp down 50°C

Development 15-20 min.

Surface development – IPA

Hard bake: 110°C for 10 min.

LOR/ PPR Recipe

Dehydration 150·C 10min

LOR3B

Spinning 15sec 300rpm

30sec 6000 Rpm

Pre bake- 150·c Time- 5min

S-1813

Spinning 15sec 300rpm

30sec 6000 Rpm

Pre bake- 90·c Time- 4min

Exposure dose - 60mJ/Cm²

MF-319 developer

PPR Recipe

Dehydration at 120 C for 10 min.

Dispense negative photoresist (S-1813) on silicon wafer

Spin at 300 RPM for 15 sec.

Spin at 3000 RPM for 30 sec.

Soft bake:

3min. at 90C

Exposure Energy: 80mJ/cm²

Development in MF-319 for 30sec